



650V/8A N-Channel Junction Power MOSFET

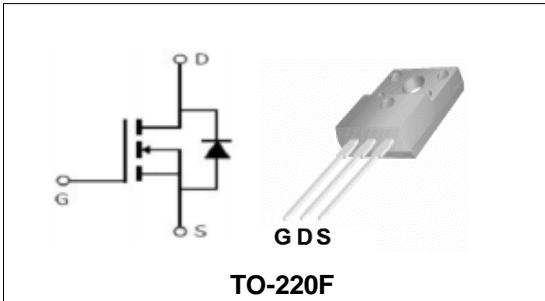
Features

- New technology for high voltage device.
- Low on-resistance and low conduction losses
- Small package
- Ultra Low Gate Charge cause lower driving requirements
- 100% Avalanche Tested

BVDSS	650	V
ID	8	A
RDSON@VGS=10V	0.9	Ω

Applications

- Power factor correction (PFC)
- Switched mode power supplies(SMPS)
- Uninterruptible Power Supply (UPS)

**Order Information**

Product	Package	Marking	Tube	Carton
PTF8N65	TO-220F	PTF8N65	50PCS	5000PCS

Absolute Maximum Ratings

Symbol	Parameter	Rating	Unit
Common Ratings (TC=25°C Unless Otherwise Noted)			
V _{(BR)DSS}	Drain-Source Breakdown Voltage	650	V
V _{GS}	Gate-Source Voltage	±30	V
T _J	Maximum Junction Temperature	150	°C
T _{STG}	Storage Temperature Range	-55 to 150	°C
I _S	Diode Continuous Forward Current	8	A
Mounted on Large Heat Sink			
P _D	Single Pulse Avalanche Energy (Note1)	49	W
I _{DM}	Pulse Drain Current Tested (Silicon Limit) (Note2)	TC =25°C	28
I _D	Continuous Drain current	TC =25°C	7
E _{AS}	Avalanche energy (Note1)	TC =25°C	mJ
R _{θJC}	Thermal Resistance Junction-to-Case (Note3)		2.5 °C/W

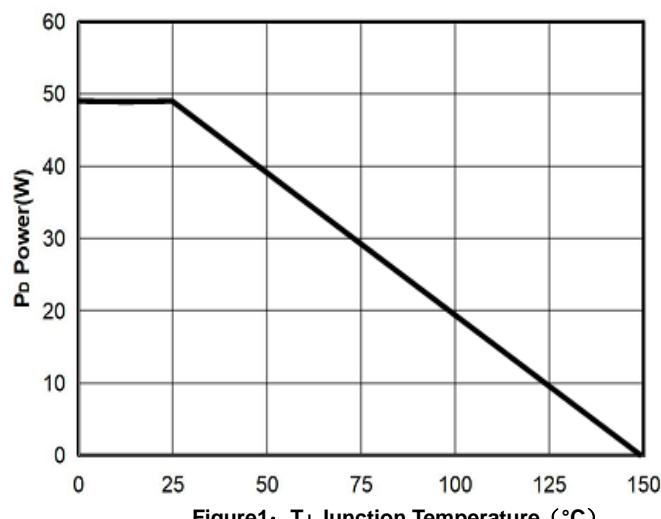
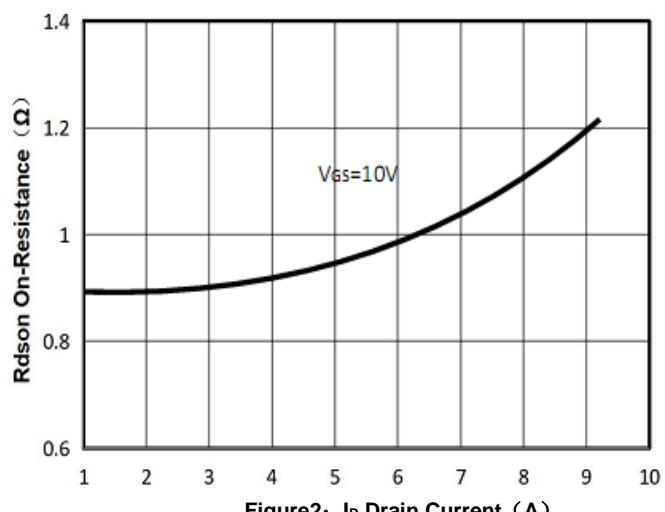
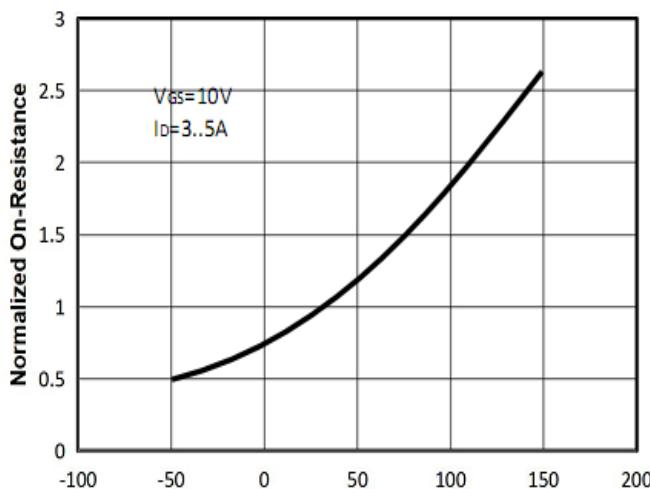
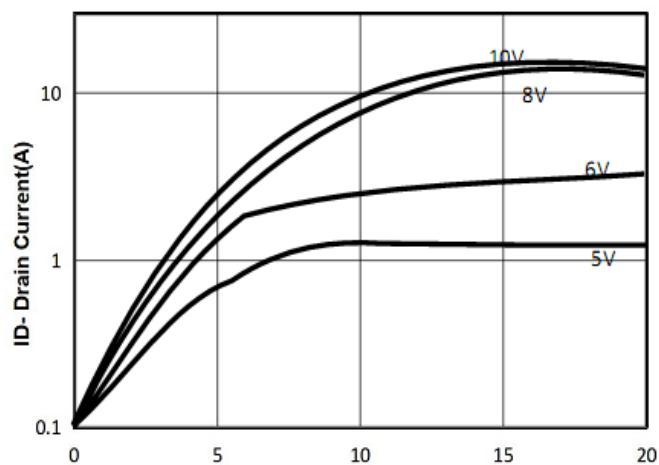
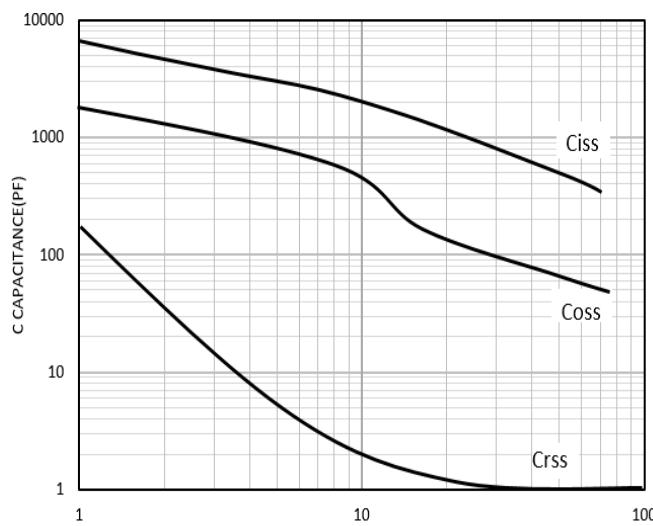
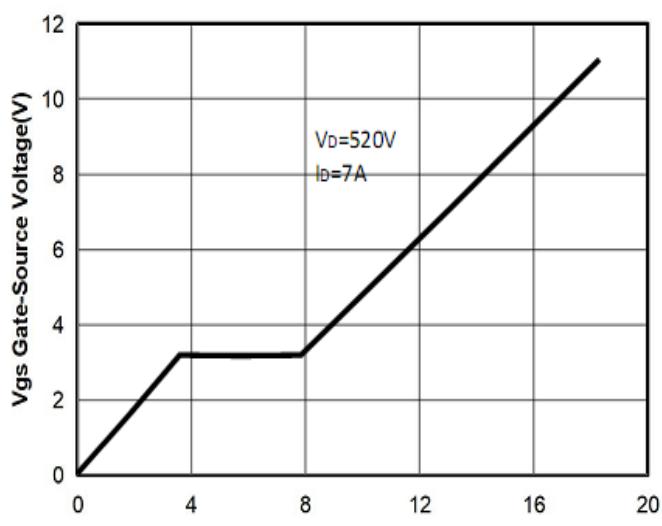


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Symbol	Parameter	Condition	Min.	Typ.	Max.	Unit
Static Electrical Characteristics @ TJ = 25°C (unless otherwise stated)						
$V_{(BR)DSS}$	Drain- Source Breakdown Voltage	$VGS=0V$ $ID=250\mu A$	650	--	--	V
I_{DSS}	Zero Gate Voltage Drain current	$VDS=650V, VGS=0V$	--	--	1	μA
I_{GSS}	Gate-Body Leakage Current	$VGS=\pm 30V, VDS=0V$	--	--	± 100	nA
$V_{GS(TH)}$	Gate Threshold Voltage	$VDS=VGS, ID=250\mu A$	2	3	4	V
$R_{DS(ON)}$	Drain-Source On-State Resistance (Note4)	$VGS=10V, ID=4A$	--	0.9	1.1	Ω
Dynamic Electrical Characteristics @ TJ = 25°C (unless otherwise stated) (Note5)						
C_{iss}	Input Capacitance	$VDS=25V,$ $VGS=0V,$ $F=1MHz$	--	980	--	pF
C_{oss}	Output Capacitance		--	108	--	pF
C_{rss}	Reverse Transfer Capacitance		--	4.8	--	pF
Q_g	Total Gate Charge	$VDS=520V,$ $ID=7A,$ $VGS=10V$	--	18	--	nC
Q_{gs}	Gate-Source Charge		--	4.3	--	nC
Q_{gd}	Gate-Drain Charge		--	3.9	--	nC
Switching Characteristics (Note5)						
$t_{d(on)}$	Turn-on Delay Time	$VDD=300V,$ $ID=7A,$ $VGS=10V$	--	27	--	nS
t_r	Turn-on Rise Time		--	18	--	nS
$t_{d(off)}$	Turn-off Delay Time		--	57	--	nS
t_f	Turn-off Fall Time		--	23	--	nS
Source- Drain Diode Characteristics@ TJ = 25°C (unless otherwise stated)						
V_{SD}	Forward on voltage	$IS=8A, VGS=0V$	--	0.85	1.4	V

Note:

- Limited by TJmax, starting TJ = 25° C, RG = 25Ω, VD = 50V, VGS = 10V. Part not recommended for use above this value.
- Repetitive Rating: Pulse width limited by maximum junction temperature.
- Surface Mounted on FR4 Board, t ≤ 10 sec.
- Pulse Test: pulse width ≤ 300 us, duty cycle ≤ 2%.
- Guaranteed by design, not subject to production testing.

**650V/8A N-Channel Junction Power MOSFET
Typical Characteristics**

Figure1: TJ Junction Temperature (°C)

Figure2: Id Drain Current (A)

Figure3: TJ Junction Temperature (°C)

Figure4: VDS Drain-Source Voltage (V)

Figure5: VDS Drain-Source Voltage (V)

Figure6: Qg Gate Charge (nC)

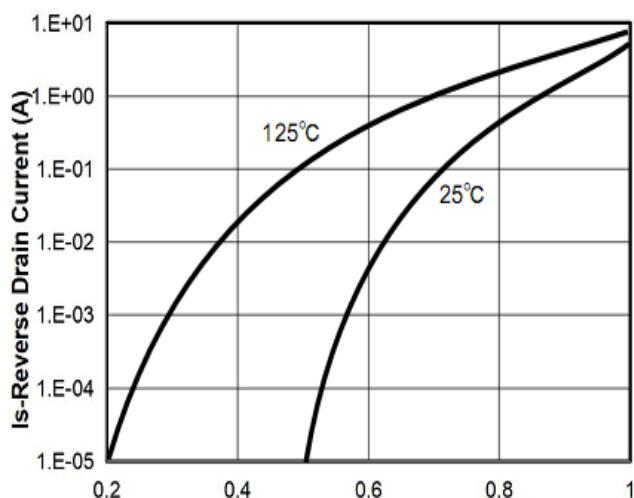
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Figure 7: V_{sd} Source-Drain Voltage (V)

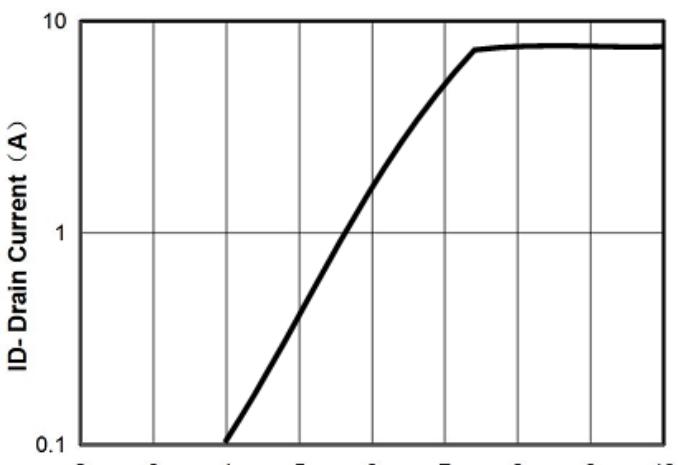


Figure 8: V_{gs} Gate-Source Voltage (V)

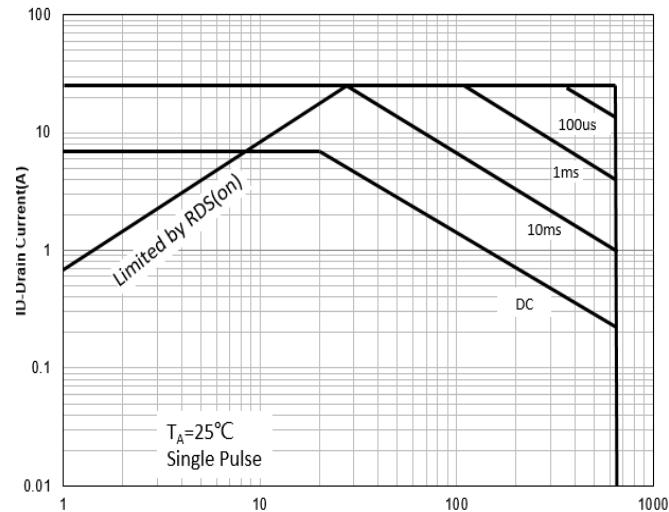


Figure 9: V_{sd} Drain -Source Voltage (V)

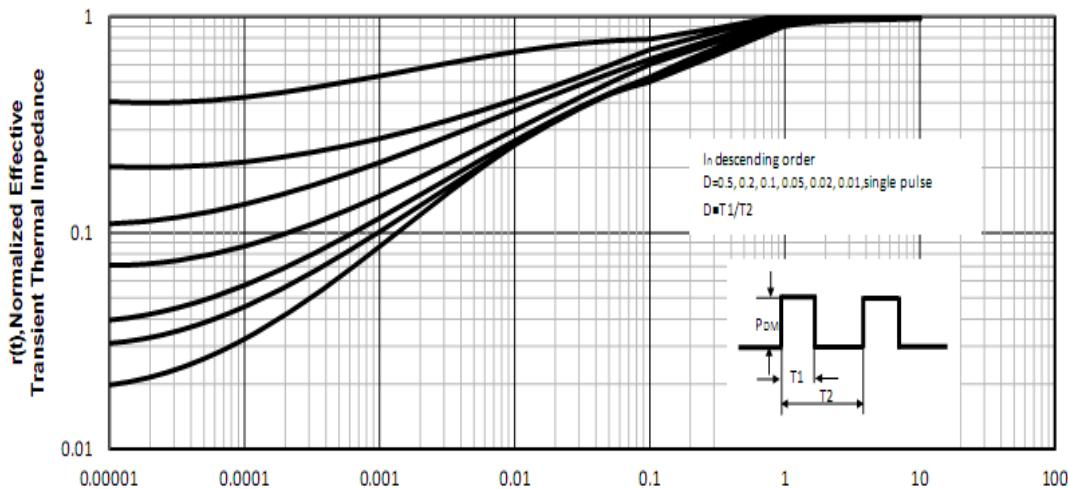
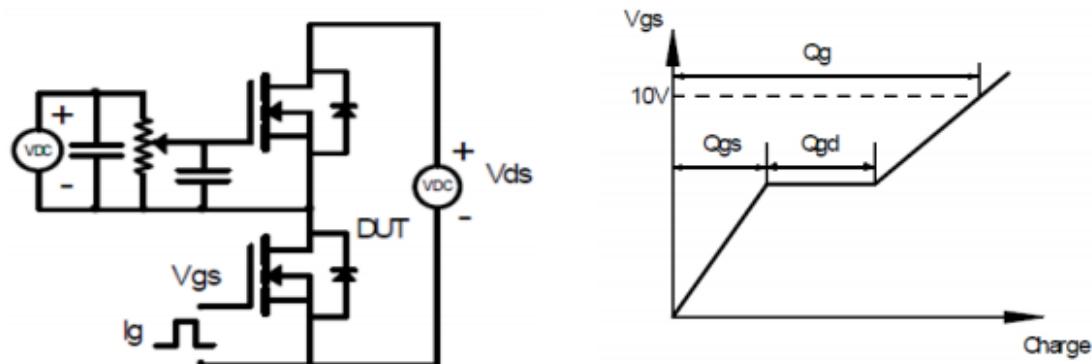
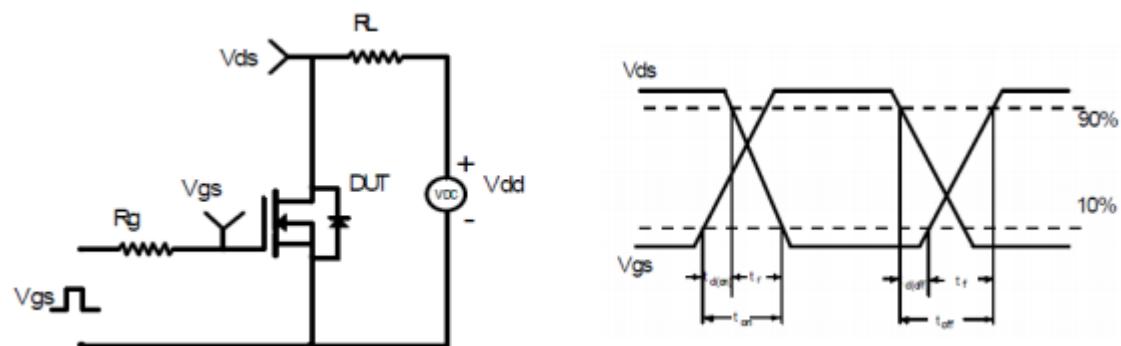
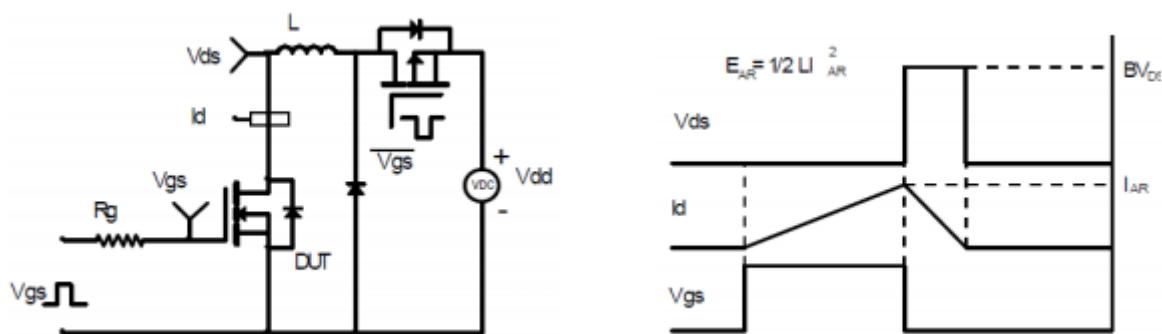
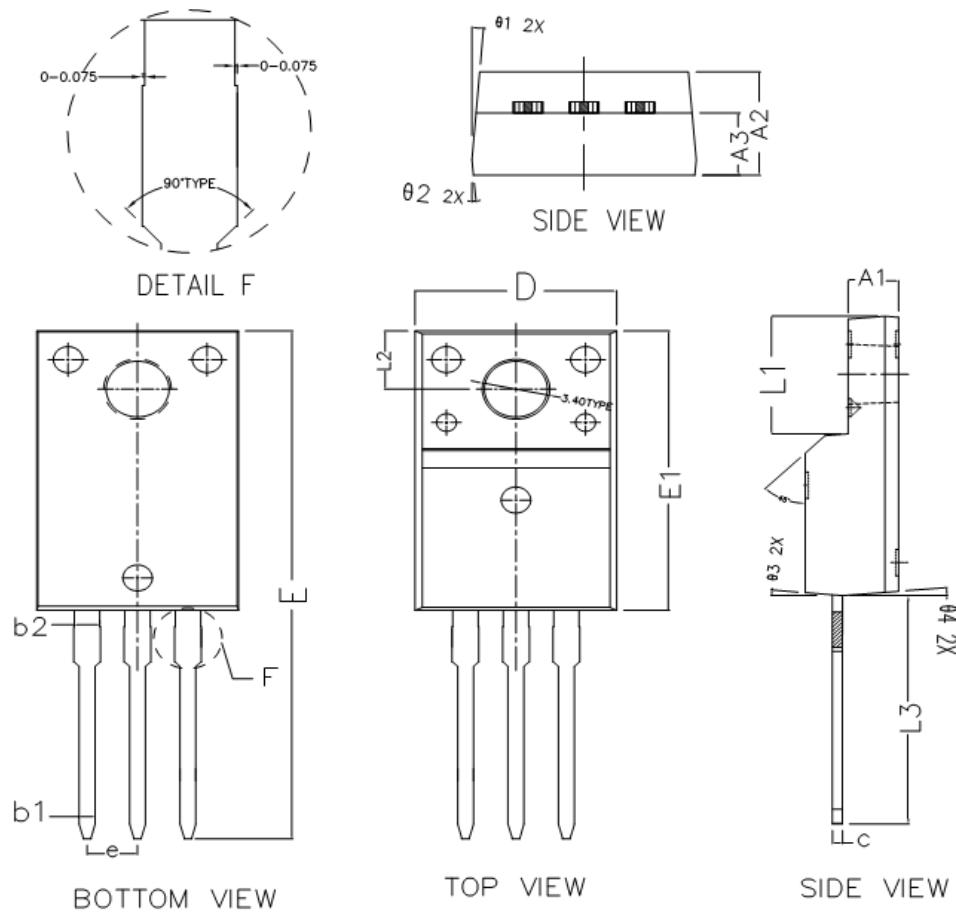


Figure 10: Square Wave Pulse Duration (sec)

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Test Circuit and Waveform:

Figure A Gate Charge Test Circuit & Waveforms

Figure B Switching Test Circuit & Waveforms

Figure C Unclamped Inductive Switching Circuit & Waveforms

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TO-220F Package Outline Dimensions (Units: mm)


COMMON DIMENSIONS (UNITS OF MEASURE IS mm)			
	MIN	NORMAL	MAX
A1	2.440	2.540	2.640
A2	4.600	4.700	4.800
A3	2.730	2.830	2.930
b1	0.750	0.800	0.850
b2	1.230	1.280	1.330
c	0.450	0.500	0.550
D	10.060	10.160	10.260
E	28.650	28.850	29.050
E1	15.770	15.870	15.970
e	2.54TYPE		
L1	6.68REF		
L2	3.30REF		
L3	12.830	12.980	13.130
θ1	5° TYPE		
θ2	5° TYPE		
θ3	5° TYPE		
θ4	5° TYPE		